

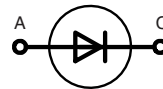
# Power Schottky Rectifier

$$I_{FAV} = 40 \text{ A}$$

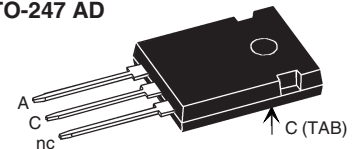
$$V_{RRM} = 8 \text{ V}$$

$$V_F = 0.23 \text{ V}$$

$V_{RSM}$	$V_{RRM}$	Type
V	V	
8	8	DSS 40-0008D



TO-247 AD



A = Anode, C = Cathode, TAB = Cathode  
nc = not connected

Symbol	Conditions	Maximum Ratings	
$I_{FRMS}$		70	A
$I_{FAV}$	$T_C = 135^\circ\text{C}$ ; rectangular, $d = 0.5$	40	A
$I_{FAV}$	$T_C = 135^\circ\text{C}$ ; rectangular, $d = 0.5$ ; per device	80	A
$I_{FSM}$	$T_{VJ} = 45^\circ\text{C}$ ; $t_p = 10 \text{ ms}$ (50 Hz), sine	600	A
$E_{AS}$	$I_{AS} = 40 \text{ A}$ ; $L = 100 \mu\text{H}$ ; $T_{VJ} = 25^\circ\text{C}$ ; non repetitive	80	mJ
$I_{AR}$	$V_A = 1.5 \cdot V_{RRM}$ typ.; $f = 10 \text{ kHz}$ ; repetitive	4	A
$(dv/dt)_{cr}$		1000	V/ $\mu\text{s}$
$T_{VJ}$		-55...+150	$^\circ\text{C}$
$T_{VJM}$		150	$^\circ\text{C}$
$T_{stg}$		-55...+150	$^\circ\text{C}$
$P_{tot}$	$T_C = 25^\circ\text{C}$	155	W
$M_d$	mounting torque	0.8...1.2	Nm
Weight	typical	6	g

## Features

- International standard package
- Very low  $V_F$
- Extremely low switching losses
- Low  $I_{RM}$ -values
- Epoxy meets UL 94V-0

## Applications

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

## Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Symbol	Conditions	Characteristic Values	
		typ.	max.
$I_R$ ①	$T_{VJ} = 25^\circ\text{C}$ ; $V_R = V_{RRM}$	200	mA
	$T_{VJ} = 100^\circ\text{C}$ ; $V_R = V_{RRM}$	1500	mA
$V_F$	$I_F = 40 \text{ A}$ ; $T_{VJ} = 125^\circ\text{C}$	0.23	V
	$I_F = 40 \text{ A}$ ; $T_{VJ} = 25^\circ\text{C}$	0.34	V
	$I_F = 80 \text{ A}$ ; $T_{VJ} = 125^\circ\text{C}$	0.35	V
$R_{thJC}$		0.8	K/W
$R_{thCH}$		0.25	K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %  
Data according to IEC 60747 and per diode unless otherwise specified

Dimensions see Outlines.pdf

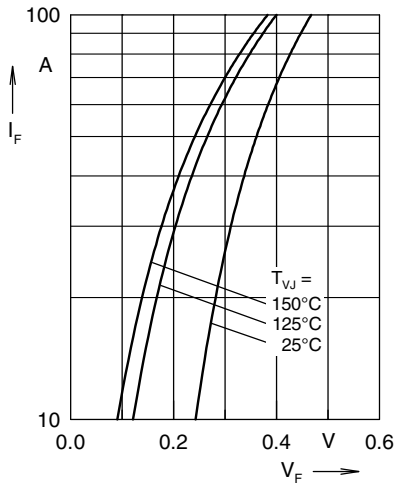


Fig. 1 Maximum forward voltage drop characteristics

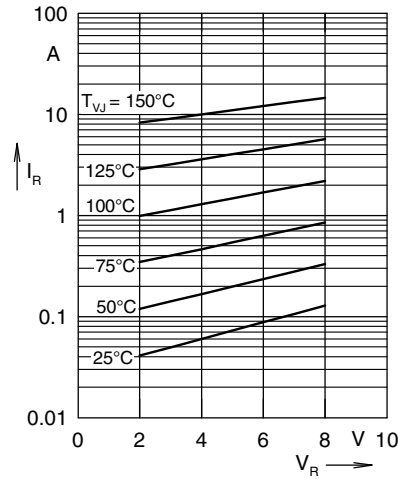


Fig. 2 Typ. value of reverse current  $I_R$  versus reverse voltage  $V_R$

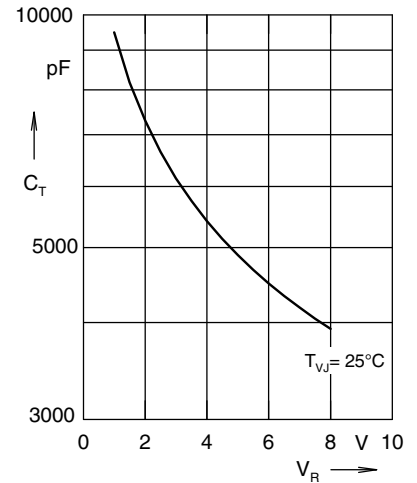


Fig. 3 Typ. junction capacitance  $C_T$  versus reverse voltage  $V_R$

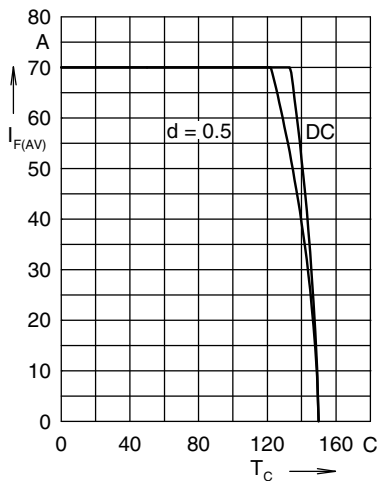


Fig. 4 Average forward current  $I_{F(AV)}$  versus case temperature  $T_C$

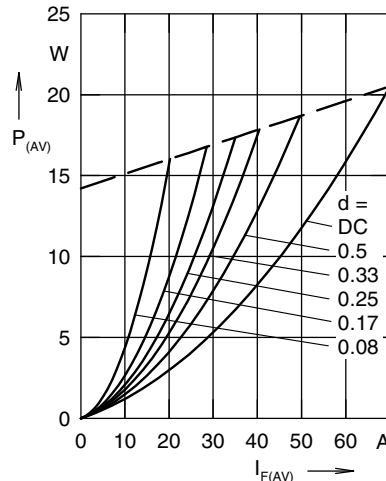


Fig. 5 Forward power loss characteristics

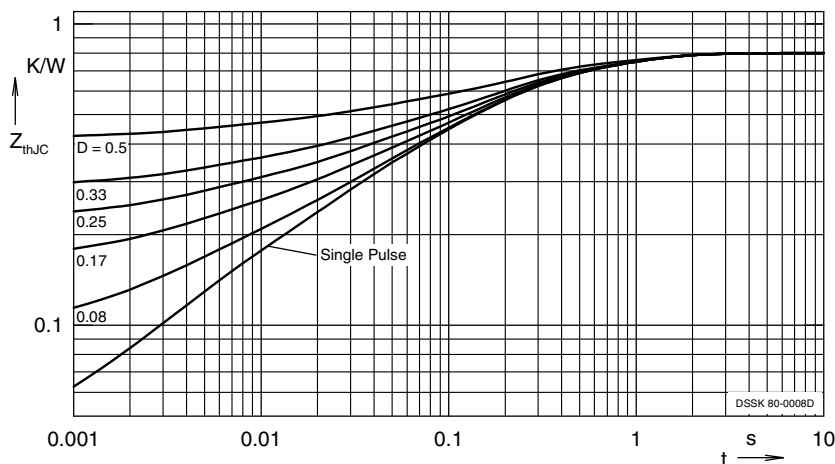


Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode

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